

ABSTRACT

METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

5 Provided is a semiconductor device which can reduce leakage of current
between wirings. Included steps are forming a first insulator over a first conductor
which is formed over substrate; forming a first hard mask thereover; forming a first
resist mask comprising a first opening, over the first hard mask; etching the first hard
mask to form a second hard mask comprising a second opening; etching the first
10 insulator using the second hard mask to form a second insulator comprising a third
opening; forming a second conductor embedded in the second opening and the third
opening; performing polishing treatment on the second hard mask and the second
conductor to form a third conductor embedded in the third opening; forming a fourth
conductor thereover; forming a second resist mask in a pattern over the fourth
15 conductor; and dry-etching the fourth conductor to form a fifth conductor. The second
hard mask can be dry-etched.

Fig. 4